

Application No.: 10/017,805

Docket No.: JCLA7245

**In The Claims:**

1. (Currently Amended) A photoresist ~~with an adjustable~~ to a polarized light response suitable for use in a photolithography process, the photoresist comprising:

a photosensitive polymer, wherein: ~~the photosensitive polymer absorbs an exposure light source to generate an optical reaction in the photolithography process; the photosensitive polymer is oriented to a specific direction by a physical method; and~~ under an electromagnetic field, and the photosensitive polymer comprises a photosensitive section for absorbing an exposure light to generate an optical reaction and an anti-etching section for increasing a resist force against a plasma etching, and the photosensitive polymer is able ~~has a response to a polarized light, wherein the response varies as~~ according to an angle variation between the specific direction and a polarization direction of the polarized light changes.

2. (Original) The photoresist according to claim 1, wherein the linear photosensitive polymer includes a linear photosensitive polymer.

3. (Original) The photoresist according to claim 2, wherein when a direction of the linear photosensitive polymer is parallel to the polarization direction of the polarized light, the liner photosensitive polymer has a maximum polarized light response, and when the direction of the linear photosensitive polymer is perpendicular to the polarization direction of the polarized light, the liner photosensitive polymer has a minimum polarized light response.

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**Claim 4. (canceled)**

5. (Currently Amended) The photoresist according to claim 14, wherein the photosensitive section includes a PMDA.

6. (Currently Amended) The photoresist according to claim 14, wherein the photosensitive section has a molecule weight of  $10^2 \sim 10^8$ .

7. (Currently Amended) The photoresist according to claim 14, wherein the anti-etching section includes ODA.

8. (Currently Amended) The photoresist according to claim 14, wherein the photosensitive section has a molecule weight as  $10^2 \sim 10^8$ .

9. (Currently Amended) The photoresist according to claim 1, wherein the physical method electromagnetic field is includes applying an electric field and when the photosensitive polymer has electric dipoles.

10. (Currently Amended) The photoresist according to claim 9, wherein applying the an electric field includes using a plasma.

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11. (Currently Amended) The photoresist according to claim 9, wherein applying the an electric field includes using a polarized ultra-violet light.

12. (Currently Amended) The photoresist according to claim 9, wherein applying the an electric field includes using a microwave.

13. (Currently Amended) The photoresist according to claim 1, wherein the ~~physieal method-electromagnetic field is includes-applying~~ a magnetic field and ~~when the~~ photosensitive polymer has magnetic dipoles.

14. (Currently Amended) The photoresist according to claim 139, wherein applying the a magnetic field includes using a plasma.

**Claims 15-30 (canceled)**